

II. Listing of Claims

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A method of manufacturing a microelectronic device, comprising:
forming a patterned feature over a substrate;
depositing a conformal polymer layer over the patterned feature and the substrate by employing
~~[[,]] wherein such depositing employs~~ a fluorine-containing plasma source and applying a first bias to the
substrate in a processing chamber; and
etching the polymer layer to expose a portion of the patterned feature and a portion of the
substrate by applying a second bias to the substrate in the processing chamber, thereby forming polymer
spacers on opposing sides of the patterned feature, wherein the second bias is substantially greater than
the first bias;
forming doped regions in the substrate, each being laterally offset from the patterned feature by
an amount about equal to a width of an adjacent one of the polymer spacers; and
removing the polymer spacers after forming the doped regions.
2. (Currently Amended) The method of claim 1 wherein the conformal polymer layer is
deposited in a chemical reactive plasma environment within the processing chamber.
3. (Original) The method of claim 1 wherein the substrate comprises diamond..
4. (Original) The method of claim 1 wherein the substrate comprises strained silicon.
5. (Original) The method of claim 1 wherein the patterned feature is a semiconductor device
gate structure.
6. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source comprises CF₄.
7. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source comprises CF₃.

8. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source comprises C_2F_2 .

9. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source comprises CH_2F_2 .

10. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source comprises CHF_3 .

11. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source comprises C_2F_6 .

12. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source comprises C_3F_8 .

13. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source comprises SF_6 .

14. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source comprises C_3F .

15. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source comprises CH_3F .

16. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source comprises a fluorocarbon.

17. (Currently Amended) The method of claim 1 wherein a flow rate of the fluorine-containing
~~chemistry~~ plasma source ranges between about 5 sccm and about 200 sccm.

18. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~
plasma source further includes a chlorine-containing gas.

19. (Original) The method of claim 18 wherein the chlorine-containing gas comprises Cl_2 and chlorocarbons.

20. (Currently Amended) The method of claim 1 wherein the fluorine-containing ~~chemistry~~ plasma source further includes a bromine-containing gas.

21. (Original) The method of claim 20 wherein the bromine-containing gas comprises HBr.

22. (Original) The method of claim 1 wherein the etching employs an oxygen-containing gas.

23. (Original) The method of claim 22 wherein the oxygen-containing gas comprises O_2 .

24. (Original) The method of claim 22 wherein the oxygen-containing gas comprises O_3 .

25. (Original) The method of claim 22 wherein the oxygen-containing gas comprises NO_2 .

26. (Original) The method of claim 22 wherein the oxygen-containing gas comprises CO_2 .

27. (Original) The method of claim 22 wherein the oxygen-containing gas comprises CO.

28. (Currently Amended) The method of claim 1 wherein the ~~step of depositing the polymer layer employs~~ first bias is a direct current (DC) bias ~~applied to the substrate~~ ranging between about 1 ~~Watts~~ Watt and about 50 Watts.

29. (Currently Amended) The method of claim 1 wherein the ~~step of depositing the polymer layer employs~~ first bias is a radio frequency (RF) bias ~~applied to the substrate~~ ranging between about 1 ~~Watts~~ Watt and about 50 Watts.

30. (Currently Amended) The method of claim 1 wherein the ~~etching the spacer employs~~ second bias is a direct current (DC) bias ~~applied to the substrate~~ ranging between about 1 ~~Watts~~ Watt and about 500 Watts.

31. (Currently Amended) The method of claim 1 wherein the ~~etching the spacer employs second~~ bias is a radio frequency (RF) bias applied to the substrate ranging between about 1 ~~Watts~~ Watt and about 500 Watts.

32. (Cancelled).

33. (Currently Amended) The method of claim ~~32~~ 1 wherein removing the polymer spacers includes etching the polymer spacers with an oxygen-containing gas.

Claims 34-36 (Withdrawn).

37. (New) The method of claim 1 wherein the steps of depositing the conformal polymer layer and etching the polymer layer collectively include biasing the substrate substantially continuously throughout the substantial duration of the depositing and etching steps, collectively.